



### General Description

The QN3109M6N is the highest performance trench N-Channel MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The QN3109M6N meet the RoHS and Green Product requirement with full function reliability approved.

### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Green Device Available

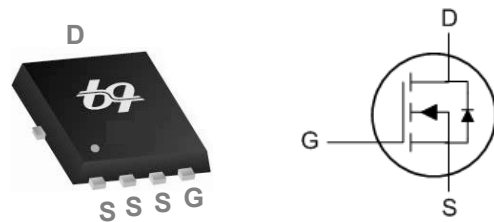
### Product Summary

BVDSS	RDSON (VGS=10V)	ID (Tc=25°C)
30V	1.5mΩ	154A

### Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

### PRPAK 5X6 Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1,7</sup>	154	A
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1,7</sup>	97	A
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	29	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	23	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	308	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	270.1	mJ
I <sub>AS</sub>	Avalanche Current	73.5	A
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup>	56	W
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>4</sup>	2	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>	---	62	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	2.2	°C/W

### Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=1\text{mA}$	---	0.008	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=30A$	---	1.2	1.5	m $\Omega$
		$V_{GS}=4.5V, I_D=15A$	---	1.9	2.5	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	---	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.3	---	$\text{mV}/^\circ\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	$\mu\text{A}$
		$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
gfs	Forward Transconductance	$V_{DS}=5V, I_D=15A$	---	62	---	S
$R_g$	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	0.9	---	$\Omega$
$Q_g$	Total Gate Charge (10V)	$V_{DS}=15V, V_{GS}=10V, I_D=15A$	---	47.6	---	nC
$Q_{g4.5V}$	Total Gate Charge (4.5V)	$V_{DS}=15V, V_{GS}=4.5V, I_D=15A$	---	21.8	---	
$Q_{gs}$	Gate-Source Charge		---	6.9	---	
$Q_{gd}$	Gate-Drain Charge		---	8.0	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V, V_{GS}=10V, R_G=3.3\Omega, I_D=15A$	---	12.1	---	ns
$T_r$	Rise Time		---	43.8	---	
$T_{d(off)}$	Turn-Off Delay Time		---	37.1	---	
$T_f$	Fall Time		---	9.0	---	
$C_{iss}$	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	3006	---	pF
$C_{oss}$	Output Capacitance		---	1941	---	
$C_{rss}$	Reverse Transfer Capacitance		---	67	---	

### Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy <sup>5</sup>	$V_{DD}=25V, L=0.1\text{mH}, I_{AS}=42.1A$	88.62	---	---	mJ

### Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1,6</sup>	$V_G=V_D=0V$ , Force Current	---	---	154	A
$I_{SM}$	Pulsed Source Current <sup>2,6</sup>		---	---	308	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V
trr	Reverse Recovery Time	$I_F=15A, dI/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	159	---	nS
Qrr	Reverse Recovery Charge		---	194	---	nC

Note :

- The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- The data tested by pulsed, pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
- The EAS data shows Max. rating. The test condition is  $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}$
- The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- The Min. value is 100% EAS tested guarantee.
- The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.
- The maximum current rating is package limited.

All information provided in this document is subjected to important notice

### Typical Characteristics

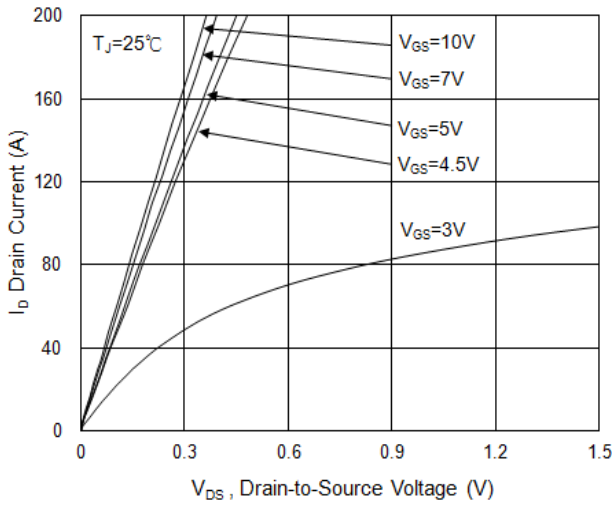


Fig.1 Typical Output Characteristics

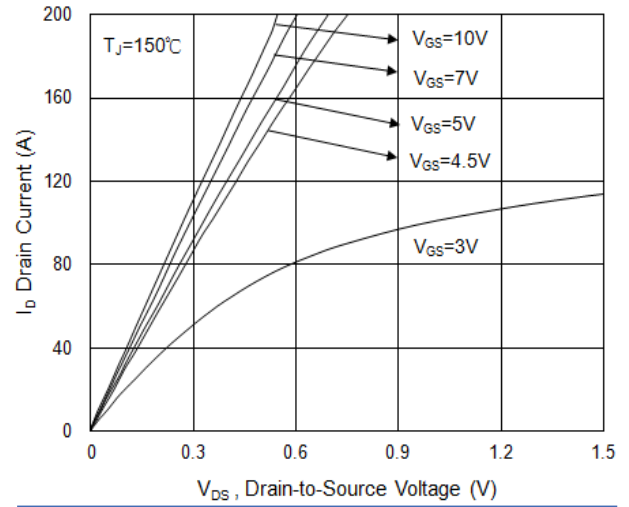


Fig.2 Typical Output Characteristics

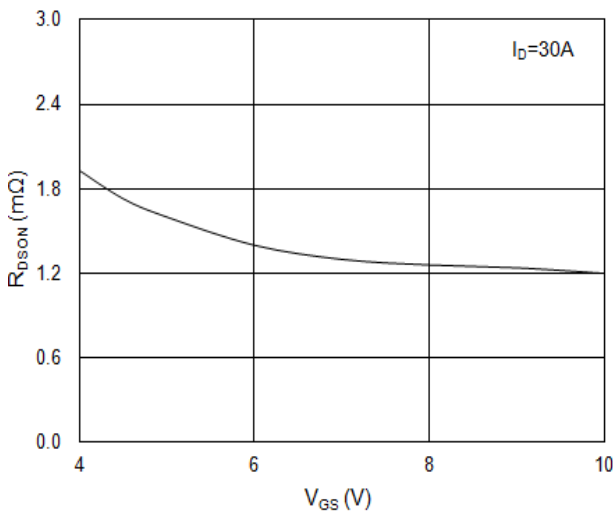


Fig.3 On-Resistance vs. Gate-Source

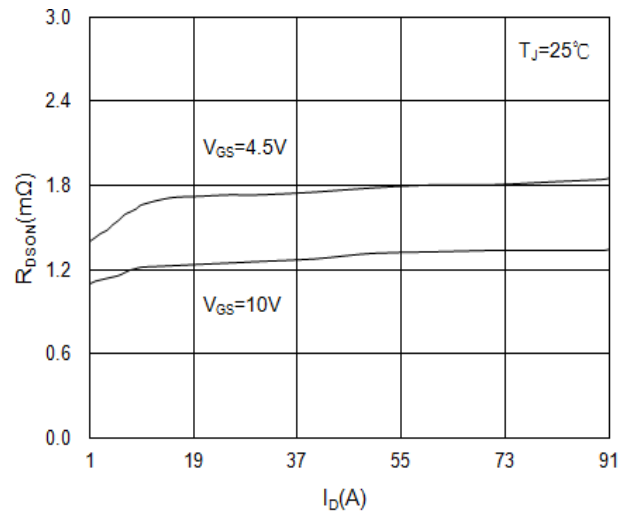


Fig.4 Drain-Source On-State Resistance

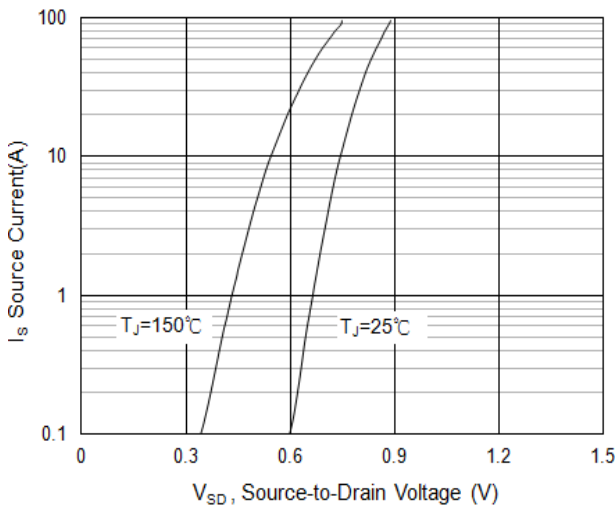


Fig.5 Forward Characteristics of Reverse

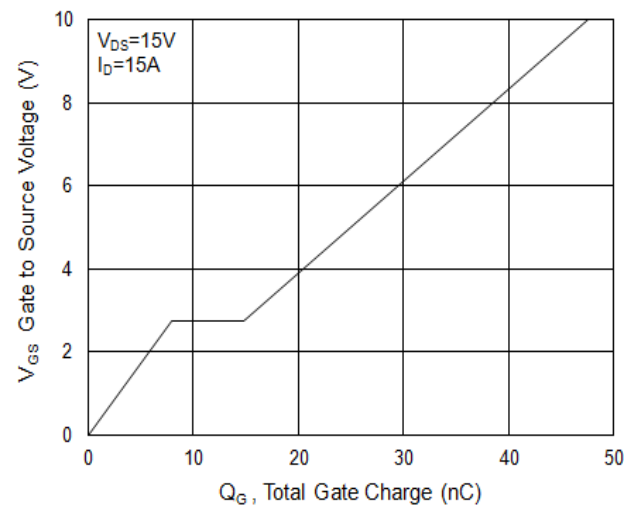


Fig.6 Gate-Charge Characteristics

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## N-Channel 30V Fast Switching MOSFET

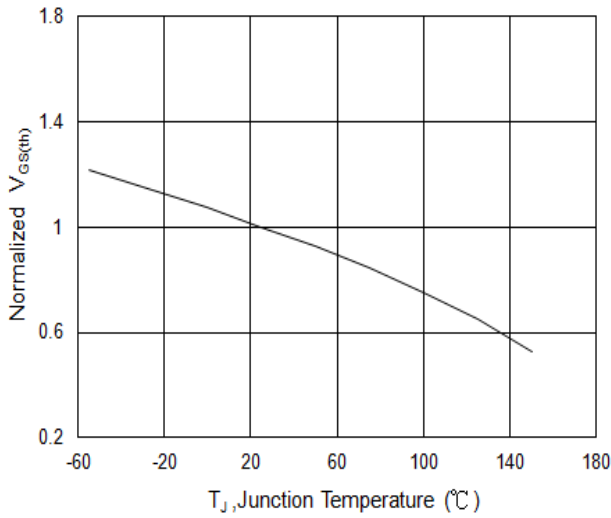


Fig.7 Normalized V<sub>GS(th)</sub> vs. T<sub>J</sub>

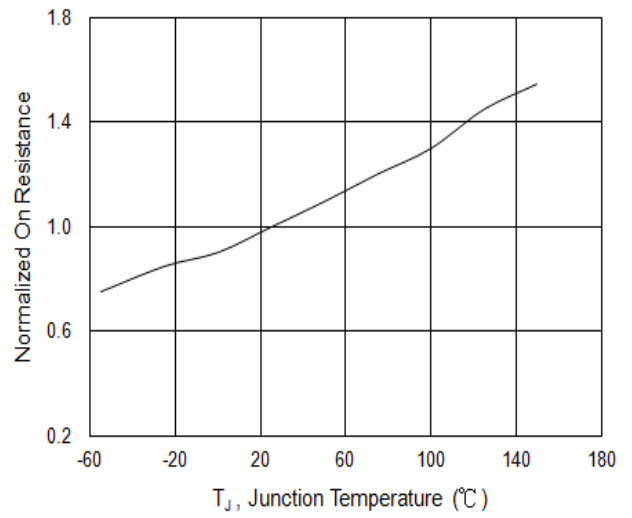


Fig.8 Normalized R<sub>DS(on)</sub> vs. T<sub>J</sub>

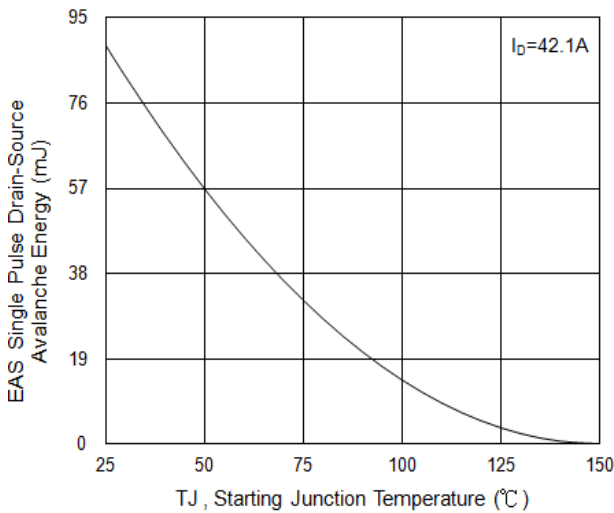


Fig.9 Single Pulse Avalanche Energy

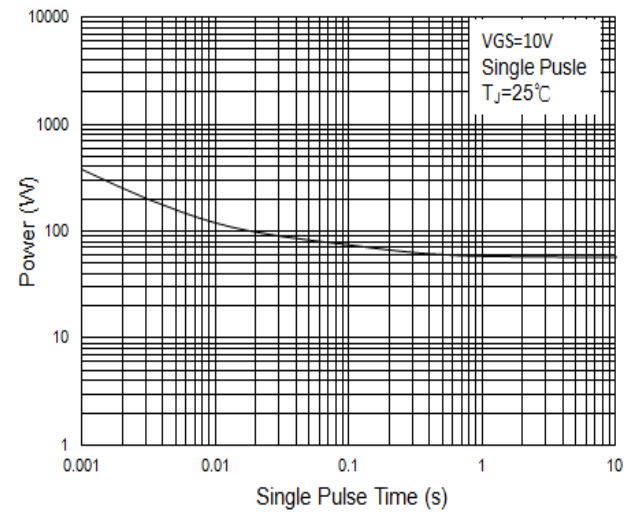


Fig.10 Single Pulse Maximum Power Dissipation

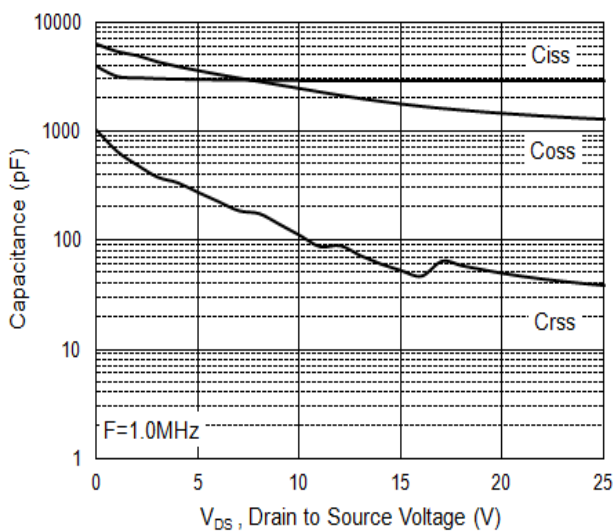


Fig.11 Capacitance

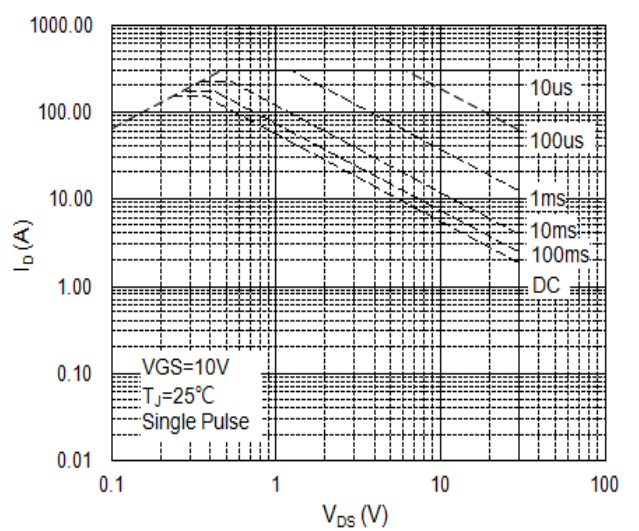
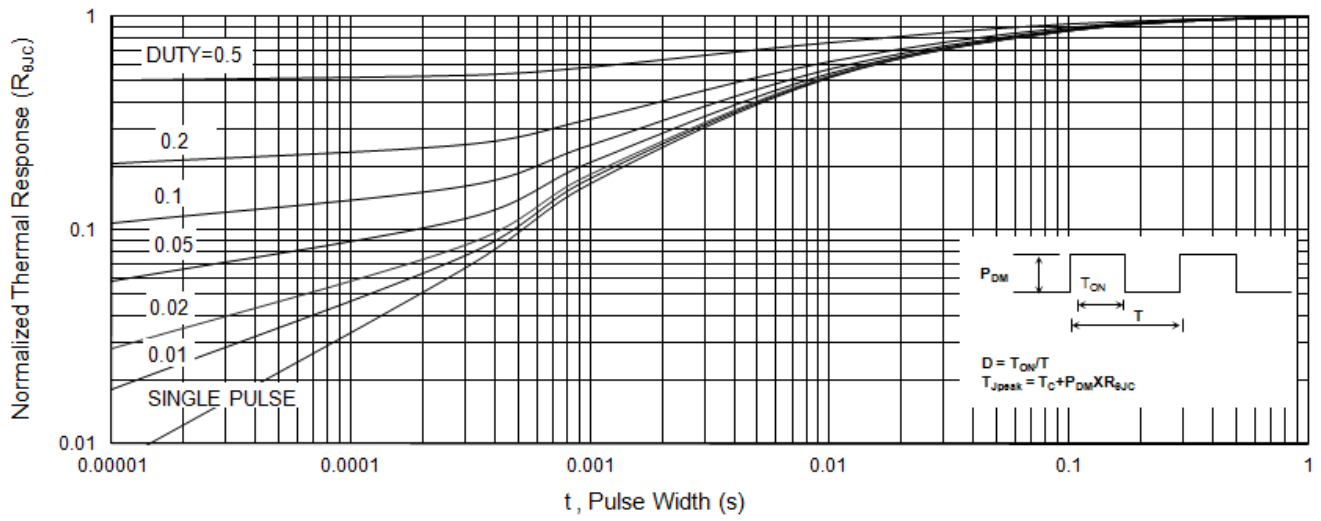


Fig.12 Safe Operating Area



**Fig.13 Transient Thermal Impedance**

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